

Docket No.: 60188-131



PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of

Kyoko HIRATA, et al.

: Attn: APPLICATIONS BRANCH

Serial No.: 10/009,842

Filed: December 17, 2001

For: SEMICONDUCTOR DEVICE

RECEIVED  
MAR 15 2002  
TECHNOLOGY CENTER 2800

2811  
#9  
PRE  
Amgt  
8:21:02  
art

SUPPLEMENTAL PRELIMINARY AMENDMENT

Hon. Assistant Commissioner for Patents  
Washington, DC 20231

Sir:

Prior to examination of the above-referenced application, please amend the application as follows:

IN THE SPECIFICATION:

1. Please replace the paragraph beginning at page 3, line 24, continuing on to page 4, with the following rewritten paragraph:

6' --The P<sup>+</sup> diffusion region **122** and the N<sup>+</sup> diffusion region **112** are formed in the N-well region **130**, and a pn junction is formed on a junction face between the P<sup>+</sup> diffusion region **122** and the N-well region **130**. Therefore, a diode can be constituted by using the P<sup>+</sup> diffusion region **122** as an anode and the N<sup>+</sup> diffusion region **112** as a cathode. In the diode element **1000**, one diode includes a junction of a pair of p and n, and therefore as the pn junction area (i.e., the bottom area of the P<sup>+</sup> diffusion region **122**) increases, the current capacity of the diode element